RENESAS

R1WV6416R Series

64Mb Advanced LPSRAM (4M word x 16bit / 8M word x 8bit)

REJ03C0368-0100 Rev.1.00 2009.05.07

Description

The R1WV6416R Series is a family of low voltage 64-Mbit static RAMs organized as 4,194,304-word by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1WV6416R Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The R1WV6416R Series is provided in 48-pin thin small outline package [TSOP (I): 12mm x 20mm with pin pitch of 0.5mm], 52-pin micro thin small outline package [µTSOP (II): 10.79mm x 10.49mm with pin pitch of 0.4mm] and 48-ball fine pitch ball grid array [f-BGA] package. It gives the best solution for compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

Features

- Single 2.7~3.6V power supply
- Small stand-by current: 8 µA (3.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS1#, CS2, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

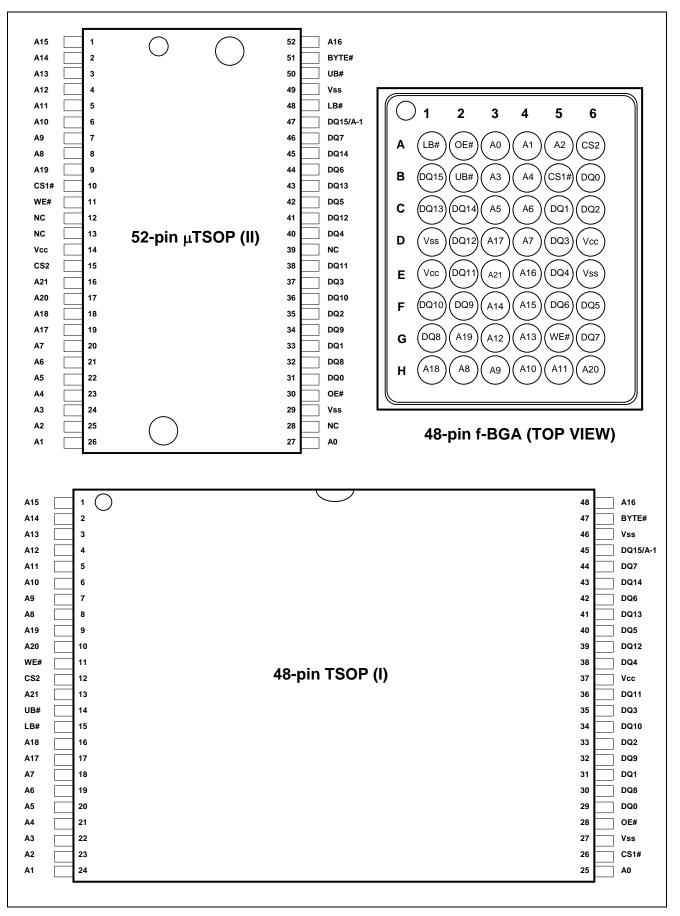
Type No.	Access time	Package
R1WV6416RSA-5S%	55 ns	12mm x 20mm 48-pin plastic TSOP (I)
R1WV6416RSA-7S%	70 ns	(normal-bend type) (48P3R)
R1WV6416RSD-5S%	55 ns	350 mil 52-pin plastic μ-TSOP (II)
R1WV6416RSD-7S%	70 ns	(normal-bend type) (52PTG)
R1WV6416RBG-5S%	55 ns	f DCA 0.75mm nitch 49 holl
R1WV6416RBG-7S%	70 ns	f-BGA 0.75mm pitch 48-ball

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%	Temperature Range						
R	0 ~ +70 °C						
I	-40 ~ +85 °C						



Pin Arrangement



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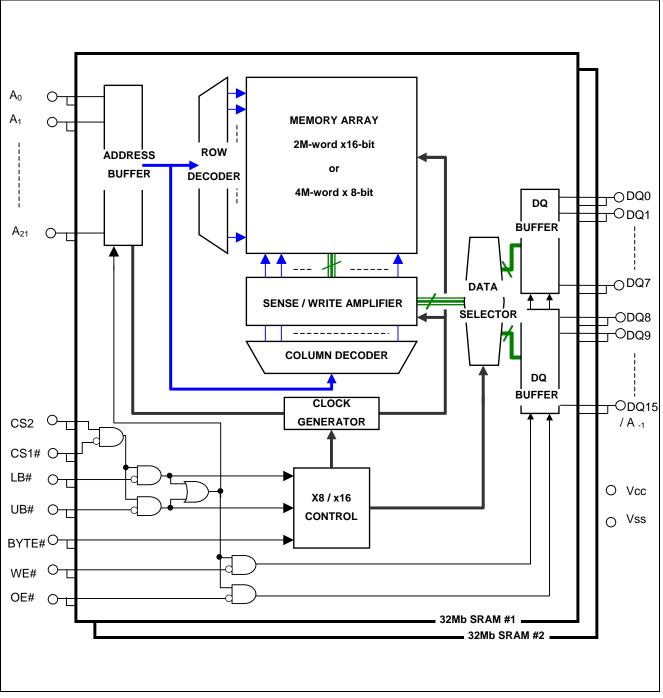
Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A21	Address input (word mode)
A-1 to A21	Address input (byte mode)
DQ0 to DQ15	Data input/output
CS1#	Chip select 1
CS2	Chip select 2
WE#	Write enable
OE#	Output enable
LB#	Lower byte enable
UB#	Upper byte enable
BYTE#	Byte control mode enable
NC	Non connection

Note: BYTE# pin is supported for 48-pin TSOP (I) and 52-pin μ TSOP (II) packages.



Block Diagram



Note: BYTE# pin is supported for 48-pin TSOP (I) and 52-pin μ TSOP (II) packages.



Operation Table

CS1#	CS2	BYTE#	LB#	UB#	WE#	OE#	DQ0~7	DQ8~14	DQ15	Operation
Н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand-by
Х	L	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand-by
Х	Х	Н	Н	Н	Х	Х	High-Z	High-Z	High-Z	Stand-by
L	Н	Н	L	H	L	Х	Din	High-Z	High-Z	Write in lower byte
L	Н	Н	L	Н	Н	L	Dout	High-Z	High-Z	Read in lower byte
L	Н	Н	L	H	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	Н	Н	L	L	Х	High-Z	Din	Din	Write in upper byte
L	Н	Н	Н	L	Н	L	High-Z	Dout	Dout	Read in upper byte
L	Н	Н	Н	L	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	Н	L	L	L	Х	Din	Din	Din	Word write
L	Н	Н	L	L	Н	L	Dout	Dout	Dout	Word read
L	Н	Н	L	L	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	L	L	L	L	Х	Din	High-Z	A-1	Byte write
L	Н	L	L	L	Н	L	Dout	High-Z	A-1	Byte read
L	Н	L	L	L	Н	Н	High-Z	High-Z	A-1	Output disable

Note1. H: $V_{IH} \quad L{:}V_{IL} \quad X{:} \; V_{IH} \; or \; V_{IL}$

2. BYTE# pin is supported for 48-pin TSOP (I) and 52-pin μTSOP (II) packages.

3. When apply BYTE# ="L", please assign LB#=UB#="L".

Absolute Maximum Ratings

Parameter	Symbol		Value	unit	
Power supply voltage relative to Vss	Vcc		-0.5 to +4.6	V	
Terminal voltage on any pin relative to Vss	VT		-0.5 ^{*1} to Vcc+0.3 ^{*2} V		
Power dissipation	PT		0.7	W	
	Topr ^{*3}	R ver.	0 to +70	°C	
Operation temperature	горг	l ver.	-40 to +85	°C	
Storage temperature range	Tstg		-65 to 150	°C	
Ctorage temperature range under bigs	Tbias ^{*3}	R ver.	0 to +70	°C	
Storage temperature range under bias	TUIAS	l ver.	-40 to +85	°C	

Note 1. –2.0V in case of AC (Pulse width ≤30ns)

2. Maximum voltage is +4.6V.

3. Ambient temperature range depends on R/I-version. Please see table on page 1.



Recommended Operating Conditions

Parameter		Symbol	Min.	Тур.	Max.	Unit	Note
Supply voltage		Vcc	2.7	3.0	3.6	V	
		Vss	0	0	0	V	
Input high voltage	Input high voltage		2.4	-	Vcc+0.2	V	
Input low voltage	Input low voltage		-0.2	-	0.4	V	1
Ambient temperature range	R ver.	Та	0	-	+70	°C	2
	I ver.	ia	-40	-	+85	°C	2

Note 1. –2.0V in case of AC (Pulse width \leq 30ns)

2. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit		Test conditions ^{*3}		
Input leakage current	I _{LI}	-	-	1	μA	Vin = Vss to Vcc			
Output leakage current	I _{LO}	-	-	1	μΑ	$\begin{split} & \text{BYTE} \# \geq \text{Vcc -}0.2\text{V or BYTE} \# \leq 0.2\text{V} \\ & \text{CS1} \# = \text{V}_{\text{IH}} \text{ or CS2 } = \text{V}_{\text{IL}} \text{ or} \\ & \text{OE} \# = \text{V}_{\text{IH}} \text{ or WE} \# = \text{V}_{\text{IL}} \text{ or} \\ & \text{LB} \# = \text{UB} \# = \text{V}_{\text{IH}}, \text{ VI/O } = \text{Vss to Vcc} \end{split}$			
Average operating current	I _{CC1}	-	45 ^{*1}	60	mA	BYTE# ≥	e, duty =100%, II/O = 0mA Vcc -0.2V or BYTE# ≤ 0.2V _{IL} , CS2 =V _{IH} , Others = V _{IH} /V _{IL}		
	I _{CC2}	-	5 ^{*1}	10	mA	BYTE# ≥ CS1# ≤ 0	µs, duty =100%, II/O = 0mA Vcc -0.2V or BYTE# ≤ 0.2V 0.2V, CS2 ≥ V _{CC} -0.2V, -0.2V, V _{IL} ≤ 0.2V		
Standby current	I _{SB}	-	0.1 ^{*1}	0.3	mA	BYTE# ≥ CS2 =V _{IL}	Vcc -0.2V or BYTE# ≤ 0.2V		
Standby current		-	8 ^{*1}	24	μA	~+25°C	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or		
		-	14 ^{*2}	48	μΑ	~+40°C	BYTE# $\leq 0.2V$ (1) 0V $\leq CS2 \leq 0.2V$ or (2) CS4# $\geq V$ = 0.2V		
	I _{SB1}	-	-	100	μA	~+70°C	(2) CS1# \geq V _{CC} -0.2V, CS2 \geq V _{CC} -0.2V or (3) LB# = UB# \geq V _{CC} -0.2V,		
		-	-	160	μA	~+85°C	$CS1\# \le 0.2V,$ $CS2 \ge V_{CC}-0.2V$		
Output high voltage	V _{OH}	2.4	-	-	V	BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V I _{OH} = -0.5mA			
Output low voltage	V _{OL}	-	-	0.4	V	-	Vcc -0.2V or BYTE# ≤ 0.2V		

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 25°C), and not 100% tested.

2. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 40° C), and not 100% tested.

3. BYTE# pin is supported for 48-pin TSOP (I) and 52-pin μTSOP (II) packages.



Capacitance

(Ta =25°C, f =1MHz)

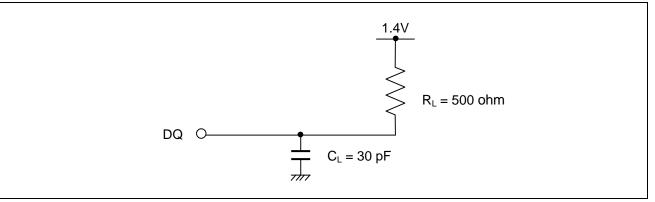
						()	/
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	Note
Input capacitance	C in	-	-	20	pF	Vin =0V	1
Input / output capacitance	C I/O	-	-	20	pF	V _{I/O} =0V	1
1	- 1/0			_		1/8 ·	

Note1.This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions (Vcc = $2.7V \sim 3.6V$, Ta = $0 \sim +70^{\circ}C / -40 \sim +85^{\circ}C^{*1}$)

- Input pulse levels: $V_{IL} = 0.4V$, $V_{IH} = 2.4V$
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Note1. Ambient temperature range depends on R/I-version. Please see table on page 1.





Read Cycle

Parameter	Symbol	R1WV64	16R**-5S	R1WV64	16R**-7S	Unit	Note
Falameter	Symbol	Min.	Max.	Min.	Max.	Onit	NOLE
Read cycle time	t _{RC}	55	-	70	-	ns	
Address access time	t _{AA}	-	55	-	70	ns	
Chip coloct copped time	t _{ACS1}	-	55	-	70	ns	
Chip select access time	t _{ACS2}	-	55	-	70	ns	
Output enable to output valid	t _{OE}	-	25	-	35	ns	
Output hold from address change	t _{OH}	10	-	10	-	ns	
LB#, UB# access time	t _{BA}	-	55	-	70	ns	
Chip poloot to output in low 7	t _{CLZ1}	10	-	10	-	ns	2,3
Chip select to output in low-Z	t _{CLZ2}	10	-	10	-	ns	2,3
LB#, UB# enable to low-Z	t _{BLZ}	5	-	5	-	ns	2,3
Output enable to output in low-Z	t _{OLZ}	5	-	5	-	ns	2,3
Chip decoloring output in high 7	t _{CHZ1}	0	20	0	25	ns	1,2,3
Chip deselect to output in high-Z	t _{CHZ2}	0	20	0	25	ns	1,2,3
LB#, UB# disable to high-Z	t _{BHZ}	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1,2,3



Write Cycle

Parameter	Symbol	R1WV6416R**-5S		R1WV64	16R**-7S	Unit	Note
Falameter	Symbol	Min.	Max.	Min.	Max.	Offic	NOLE
Write cycle time	t _{WC}	55	-	70	-	ns	
Address valid to end of write	t _{AW}	50	-	65	-	ns	
Chip select to end of write	t _{CW}	50	-	65	-	ns	5
Write pulse width	t _{WP}	40	-	55	-	ns	4
LB#, UB# valid to end of write	t _{BW}	50	-	65	-	ns	
Address setup time	t _{AS}	0	-	0	-	ns	6
Write recovery time	t _{WR}	0	-	0	-	ns	7
Data to write time overlap	t _{DW}	25	-	35	-	ns	
Data hold from write time	t _{DH}	0	-	0	-	ns	
Output enable from end of write	tow	5	-	5	-	ns	2
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1,2
Write to output in high-Z	t _{WHZ}	0	20	0	25	ns	1,2

Note1. t_{CHZ}, t_{OHZ}, t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

2. This parameter is sampled and not 100% tested.

3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.

4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.

A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low .

A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. t_{WP} is measured from the beginning of write to the end of write.

5. t_{CW} is measured from the later of CS1# going low or CS2 going high to end of write.

6. t_{AS} is measured the address valid to the beginning of write.

7. t_{WR} is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.

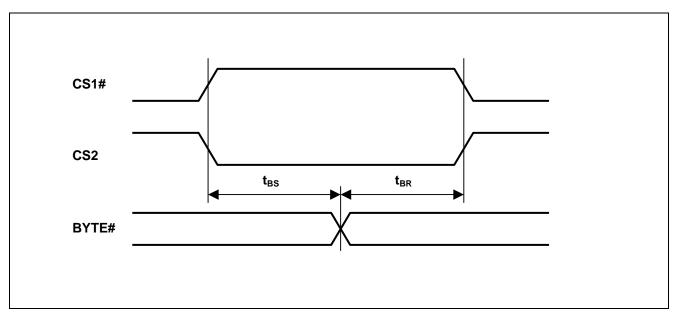


R1WV6416R Series

BYTE# Timing Conditions

Parameter	Symbol	R1WV64	16R**-5S	R1WV6416R**-7S		Unit	Note
Falametei	Symbol	Min.	Max.	Min.	Max.	Onit	NOLE
Byte setup time	t _{BS}	5	-	5	-	ms	
Byte recovery time	t _{BR}	5	-	5	-	ms	

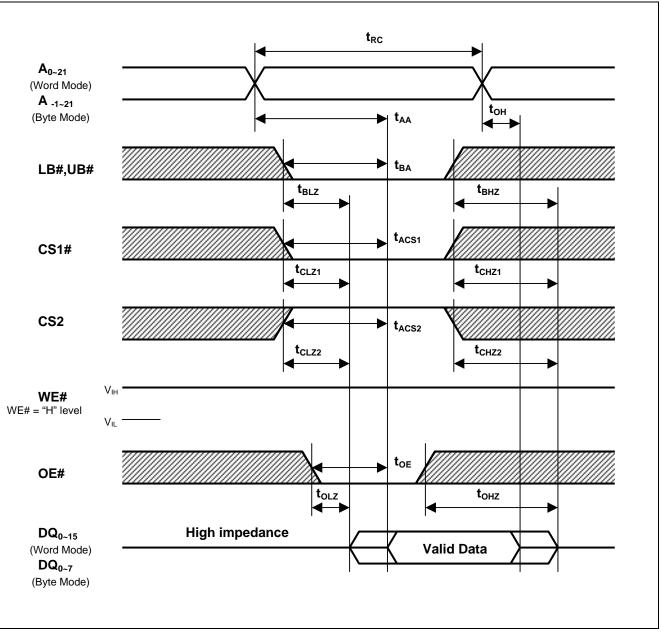
BYTE# Timing Waveforms





Timing Waveforms

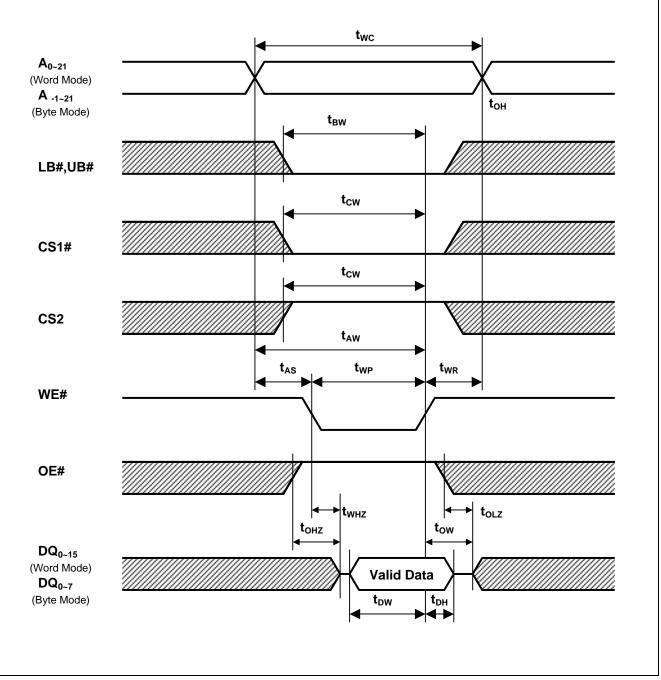
Read Cycle^{*1}



Note1. BYTE# \geq Vcc - 0.2V or BYTE# \leq 0.2V



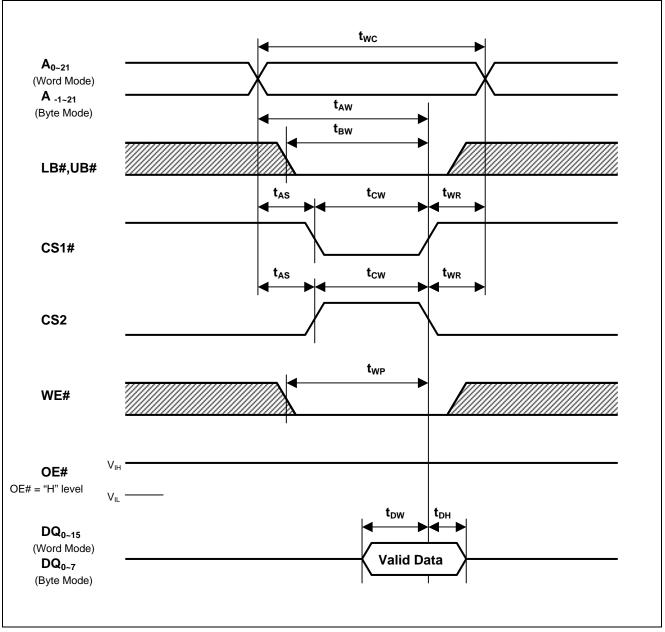
Write Cycle (1)^{*1} (WE# CLOCK)



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Note1. BYTE# \geq Vcc - 0.2V or BYTE# \leq 0.2V

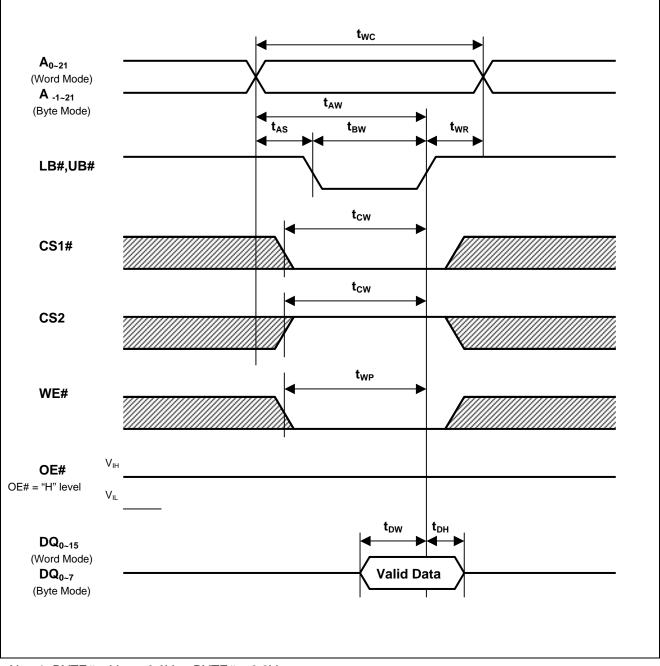
Write Cycle (2)^{*1} (CS1#, CS2 CLOCK)



Note1. BYTE# \geq Vcc - 0.2V or BYTE# \leq 0.2V



Write Cycle (3)^{*1} (LB#, UB# CLOCK)



Note1. BYTE# \geq Vcc - 0.2V or BYTE# \leq 0.2V



Parameter	Symbol	Min.	Тур	Max.	Unit	Test conditions ^{*3,4}		
V_{CC} for data retention	V _{DR}	2.0	-	3.6	V	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V or (3) LB# = UB# ≥ V _{CC} -0.2V, CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V		
Data retention current	Iccdr	-	8 ^{*1}	24	μΑ	~+25°C	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or	
		-	14 ^{*2}	48	μΑ	~+40°C	BYTE# $\leq 0.2V$ (1) 0V \leq CS2 $\leq 0.2V$ or (2) CS1# $\geq V = 0.2V$	
		-	-	100	μΑ	~+70°C	(2) CS1# \geq V _{CC} -0.2V, CS2 \geq V _{CC} -0.2V or (3) LB# = UB# \geq V _{CC} -0.2V,	
		-	-	160	μΑ	~+85°C	$CS1\# \le 0.2V,$ $CS2 \ge V_{CC} - 0.2V$	
Chip select to data retention time	t _{CDR}	0	-	-	ns	See retention waveform.		
Operation recovery time	t _R	5	-	-	ms			

Low Vcc Data Retention Characteristics

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 25° C), and not 100% tested.

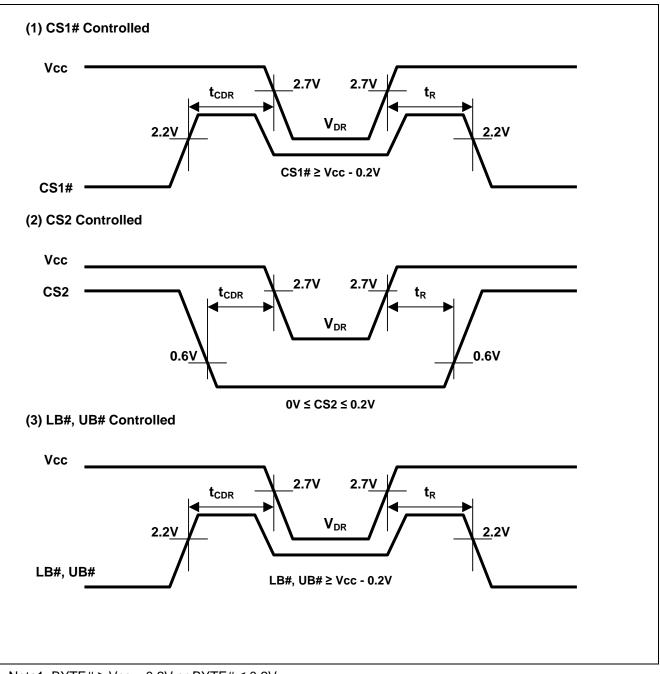
2. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 40°C), and not 100% tested.

3. BYTE# pin is supported for 48-pin TSOP (I) and 52-pin μTSOP (II) packages.

4. CS2 also controls address buffer, WE# buffer ,CS1# buffer ,OE# buffer ,LB# ,UB# buffer and Din buffer. If CS2 controls data retention mode, Vin levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be CS2 ≥ Vcc-0.2V or0V ≤ CS2 ≤ 0.2V. The other input levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state.



Low Vcc Data Retention Timing Waveforms^{*1}



Note1. BYTE# \geq Vcc - 0.2V or BYTE# \leq 0.2V



Revision History

R1WV6416R Data Sheet

		Contents pf Revision				
Rev.	Date	Page	Description			
0.01	Mar.24, 2008	-	Initial issue: Preliminary Data Sheet			
1.00	May 07, 2009	-	Finalized			
		5	Operation Table corrected			
		6	Error corrected: I _{SB} Test condition CS2=V _{IH} ->V _{IL}			

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Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

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